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| SANYO | No.1799D | 2SC3576 |
| | | NPN Epitaxial Planar Silicon Transistor |

**High h_{FE} , Low-Frequency
General-Purpose Amp Applications**

Applications

- . LF general-purpose amplifiers, various drivers, muting circuit

Features

- . Adoption of FBET process
- . High DC current gain ($h_{FE}=800$ to 3200).
- . Low collector-to-emitter saturation voltage ($V_{CE(sat)} \leq 0.5V$).
- . High V_{EBO} ($V_{EBO} \geq 15V$).

Absolute Maximum Ratings at $T_a=25^\circ C$

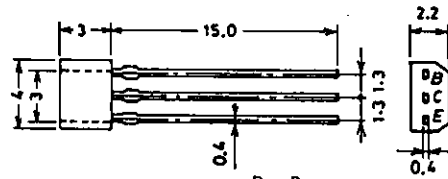
| | | | unit |
|------------------------------|-----------|-------------|------------|
| Collector to Base Voltage | V_{CBO} | 30 | V |
| Collector to Emitter Voltage | V_{CEO} | 25 | V |
| Emitter to Base Current | V_{EBO} | 15 | V |
| Collector Current | I_C | 300 | mA |
| Collector Current(Pulse) | I_{CP} | 500 | mA |
| Base Current | I_B | 60 | mA |
| Collector Dissipation | P_C | 300 | mW |
| Junction Temperature | T_j | 150 | $^\circ C$ |
| Storage Temperature | T_{stg} | -55 to +150 | $^\circ C$ |

Electrical Characteristics at $T_a=25^\circ C$

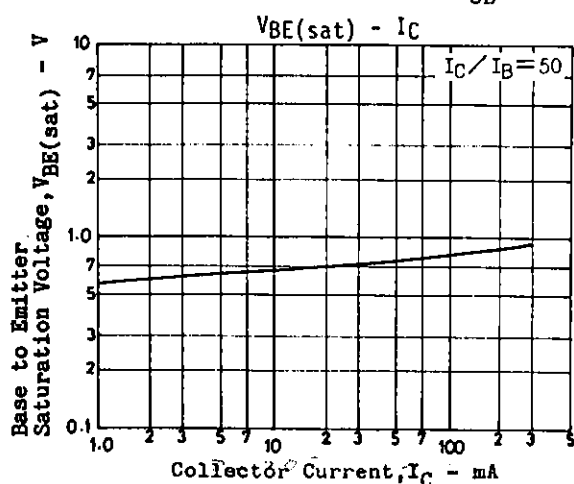
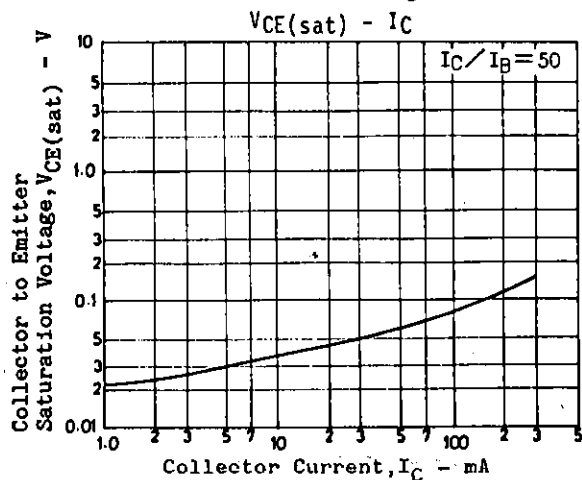
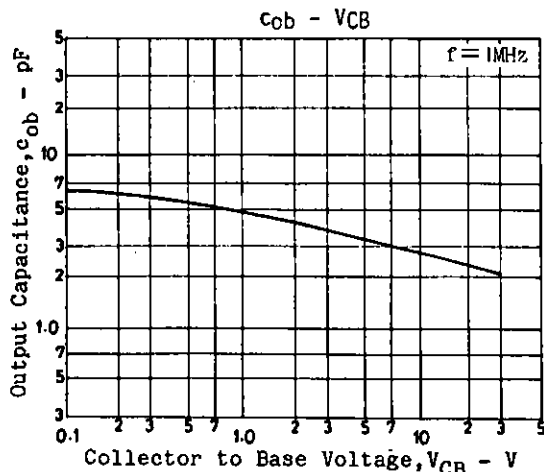
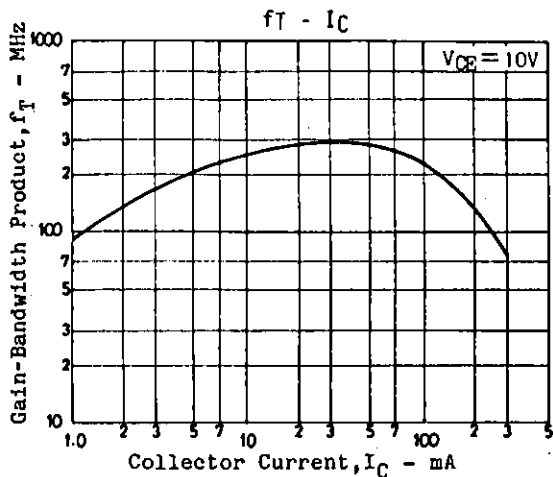
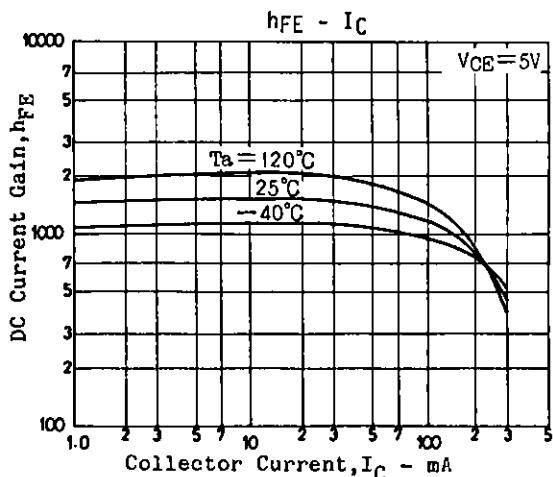
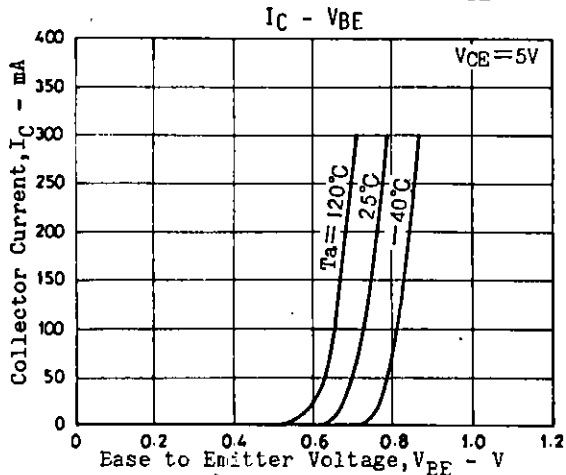
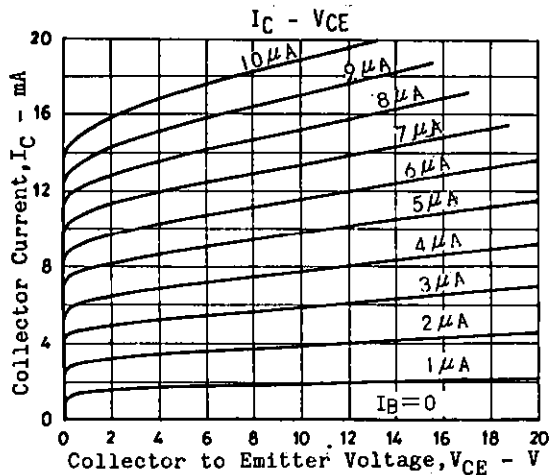
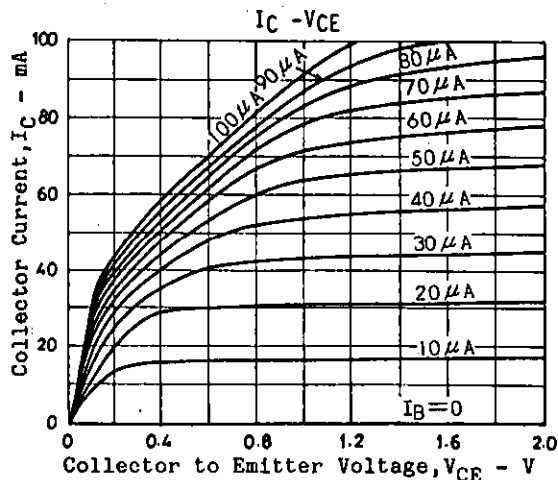
| | | | min | typ | max | unit |
|--------------------------|---------------|--------------------------|-----|------|------|---------|
| Collector Cutoff Current | I_{CBO} | $V_{CB}=20V, I_E=0$ | | | 0.1 | μA |
| Emitter Cutoff Current | I_{EBO} | $V_{EB}=10V, I_C=0$ | | | 0.1 | μA |
| DC Current Gain | h_{FE} | $V_{CE}=5V, I_C=10mA$ | 800 | 1500 | 3200 | |
| Gain-Bandwidth Product | f_T | $V_{CE}=10V, I_C=10mA$ | | 250 | | MHz |
| Output Capacitance | c_{ob} | $V_{CB}=10V, f=1MHz$ | | 2.7 | | pF |
| C-E Saturation Voltage | $V_{CE(sat)}$ | $I_C=200mA, I_B=4mA$ | | 0.12 | 0.5 | V |
| B-E Saturation Voltage | $V_{BE(sat)}$ | $I_C=200mA, I_B=4mA$ | | 0.85 | 1.2 | V |
| C-B Breakdown Voltage | $V_{(BR)CBO}$ | $I_C=10\mu A, I_E=0$ | 30 | | | V |
| C-E Breakdown Voltage | $V_{(BR)CEO}$ | $I_C=1mA, R_{BE}=\infty$ | 25 | | | V |
| E-B Breakdown Voltage | $V_{(BR)EBO}$ | $I_E=10\mu A, I_C=0$ | 15 | | | V |

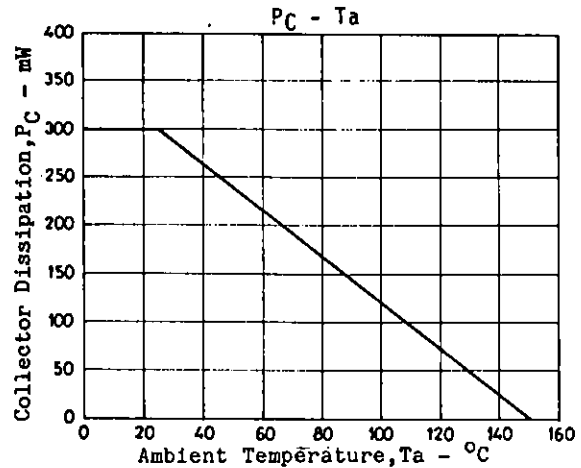
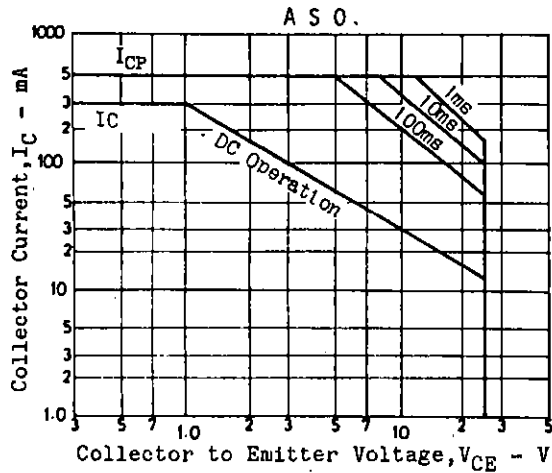
Package Dimensions 2033

(unit: mm)



B: Base
C: Collector
E: Emitter
SANYO: SPA





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